

L6562AT

Features

- Guaranteed for extreme temperature range (outdoor)
- Proprietary multiplier design for minimum THD
- Very accurate adjustable output overvoltage protection
- Ultra-low (30 µA) start-up current
- Low (2.5 mA) quiescent current
- Digital leading-edge blanking on current sense
- Disable function on E/A input
- 1% (@ T_J = 25 °C) internal reference voltage
- -600/+800 mA totem pole gate driver with active pull-down during UVLO and voltage clamp

Figure 1. Block diagram



DIP-8/SO-8 packages

Applications

PFC pre-regulators for:

- Street lighting
- IEC61000-3-2 compliant SMPS (Flat TV, monitors, desktop PC, games)
- Electronic ballast

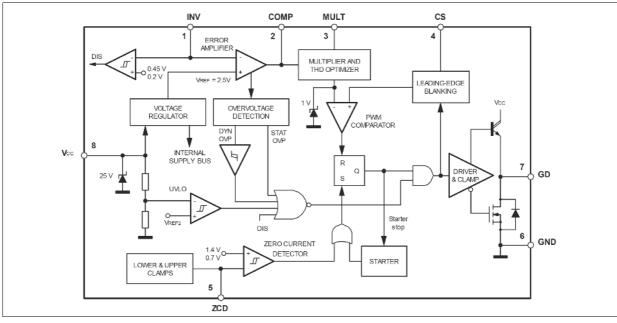


Table 1. Device summary

Order codes	Package	Packaging
L6562ATN	L6562ATN DIP-8	
L6562ATD	SO-8	Tube
L6562ATDTR		Tape and reel

Transition-mode PFC controller

1 Description

The L6562AT is a current-mode PFC controller operating in transition mode (TM). Coming with the same pin-out as its predecessors L6561 and L6562, it offers improved performance.

The highly linear multiplier includes a special circuit, able to reduce AC input current distortion, that allows wide-range-mains operation with an extremely low THD, even over a large load range.

The output voltage is controlled by means of a voltage-mode error amplifier and an accurate (1% $@T_1 = 25 \degree$ C) internal voltage reference.

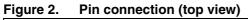
The device features extremely low consumption ($60 \ \mu A \ max$. before start-up and < 5.5 mA operating) and includes a disable function suitable for IC remote ON/OFF, which makes it easier to comply with energy saving requirements (Blue Angel, EnergyStar, Energy2000, etc.).

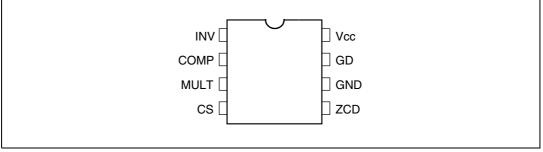
An effective two-step OVP enables to safely handle over-voltages either occurring at startup or resulting from load disconnection.

The totem-pole output stage, capable of 600 mA source and 800 mA sink current, is suitable to drive high current MOSFETs or IGBTs. This, combined with the other features and the possibility to operate with the proprietary fixed-off-time control, makes the device an excellent low-cost solution for EN61000-3-2 compliant SMPS in excess of 350 W.

2 Pin settings

2.1 Pin connection





2.2 Pin description

Pin N°	Name	Description
FIIIN	Name	Description
1	INV	Inverting input of the error amplifier. The information on the output voltage of the PFC pre-regulator is fed into this pin through a resistor divider. The pin doubles as an ON/OFF control input.
2	COMP	Output of the error amplifier. A compensation network is placed between this pin and INV to achieve stability of the voltage control loop and ensure high power factor and low THD.
3	MULT	Main input to the multiplier. This pin is connected to the rectified mains voltage via a resistor divider and provides the sinusoidal reference to the current loop.
4	CS	Input to the PWM comparator. The current flowing in the MOSFET is sensed through a resistor, the resulting voltage is applied to this pin and compared with an internal sinusoidal-shaped reference, generated by the multiplier, to determine MOSFET's turn-off. The pin is equipped with 200 ns leading-edge blanking for improved noise immunity.
5	ZCD	Boost inductor's demagnetization sensing input for transition-mode operation. A negative-going edge triggers MOSFET's turn-on.
6	GND	Ground. Current return for both the signal part of the IC and the gate driver.
7	GD	Gate driver output. The totem pole output stage is able to drive power MOSFET's and IGBT's with a peak current of 600 mA source and 800 mA sink. The high-level voltage of this pin is clamped at about 12 V to avoid excessive gate voltages in case the pin is supplied with a high Vcc.
8	Vcc	Supply voltage of both the signal part of the IC and the gate driver. The supply voltage upper limit is extended to 22 V min. to provide more headroom for supply voltage changes.

Table	2.	Pin	description
Iabio			accomption

3 Maximum ratings

Table 3. Absolute maximum ratings

Symbol	Pin	Parameter	Value	Unit
V _{CC}	8	IC supply voltage (I _{CC} \leq 20 mA)	Self-limited	V
I _{GD}	7	Output totem pole peak current	Self-limited	А
	1 to 4	Analog inputs and outputs	-0.3 to 8	V
I _{ZCD}	5	Zero current detector max. current	±10	mA

4 Thermal data

	Table 4	4.	Thern	nal	data
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Symbol	Parameter	Va	Unit		
Symbol	Farameter	SO8	DIP8	onit	
R _{thJA}	Max. thermal resistance, junction-to- ambient	150 100		°C/W	
P _{TOT}	Power dissipation @T _A = 50 °C	0.65 1		W	
TJ	Junction temperature operating range	-40 to 150		°C	
T _{STG}	Storage temperature	-55 to 150		°C	

5 Electrical characteristics

-40 °C < T_J < +125 °C, V_{CC} = 12 V, C_O = 1 nF; unless otherwise specified

 Table 5.
 Electrical characteristics

Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Supply vol	tage					
V _{CC}	Operating range	After turn-on	10.5		22.5	V
Vcc _{On}	Turn-on threshold	(1)	11.7	12.5	13.3	V
Vcc _{Off}	Turn-off threshold	(1)	9.5	10	10.5	V
Hys	Hysteresis		2.2		2.8	V
Vz	Zener voltage	I _{CC} = 20 mA	22.5	25	28	V
Supply cur	rent	•	•			
I _{start-up}	Start-up current	Before turn-on, V _{CC} = 11 V		30	60	μA
۱ _q	Quiescent current	After turn-on		2.5	3.9	mA
I _{CC}	Operating supply current	@ 70 kHz		3.5	5.5	mA
I _q	Quiescent current	During OVP (either static or dynamic) or $V_{INV} \le 150 \text{ mV}$		1.7	2.2	mA
Multiplier i	nput					
I _{MULT}	Input bias current	V _{MULT} = 0 to 4 V			-1	μA
V _{MULT}	Linear operation range		0 to 3			V
$\frac{\Delta V_{cs}}{\Delta V_{MULT}}$	Output max. slope	V _{MULT} = 0 to 1 V, V _{COMP} = Upper clamp	1	1.1		V/V
К	Gain ⁽²⁾	$V_{MULT} = 1 V, V_{COMP} = 4 V,$	0.32	0.38	0.47	V
Error ampl	ifier					
	Voltage feedback input	T _J = 25 °C	2.475	2.5	2.525	
V _{INV}	threshold	$10.5 \text{ V} < \text{V}_{\text{CC}} < 22.5 \text{ V}^{(1)}$	2.44		2.545	V
	Line regulation	V _{CC} = 10.5 V to 22.5 V		2	5	mV
I _{INV}	Input bias current	$V_{INV} = 0$ to 3 V			-1	μA
Gv	Voltage gain	Open loop	60	80		dB
GB	Gain-bandwidth product			1		MHz
I _{COMP}	Source current	V _{COMP} = 4 V, V _{INV} = 2.4 V	-2	-3.5	-5	mA
	Sink current	V _{COMP} = 4 V, V _{INV} = 2.6 V	2.5	4.5		mA
V	Upper clamp voltage	I _{SOURCE} = 0.5 mA	5.1	5.7	6	V
V _{COMP}	Lower clamp voltage	$I_{SINK} = 0.5 \text{ mA}^{(1)}$	2.1	2.25	2.4	V
V _{INVdis}	Disable threshold		150	200	250	mV
V _{INVen}	Restart threshold		380	450	520	mV

Symbol	Parameter	Test condition	Min	Тур	Max	Unit
Output ove				71		
Output ove	-	1		1		-
I _{OVP}	Dynamic OVP triggering current		19.5	27	30.5	μA
Hys	Hysteresis	(3)		20		μA
	Static OVP threshold	(1)	2.1	2.25	2.4	V
Current se	nse comparator					
I _{CS}	Input bias current	$V_{CS} = 0$			-1	μA
t _{LEB}	Leading edge blanking		100	200	300	ns
td _(H-L)	Delay to output			175		ns
V _{CS}	Current sense clamp	V _{COMP} = Upper clamp, Vmult = 1.5 V	1.0	1.08	1.16	V
Vee	Current conce offect	V _{MULT} = 0		25		<u> </u>
Vcs _{offset}	Current sense offset	V _{MULT} = 2.5 V		5		mV
Zero curre	nt detector					
V _{ZCDH}	Upper clamp voltage	$I_{ZCD} = 2.5 \text{ mA}$	5.0	5.7	6.5	V
V _{ZCDL}	Lower clamp voltage	I _{ZCD} = - 2.5 mA	-0.5	0	0.5	V
V _{ZCDA}	Arming voltage (positive-going edge)	(3)		1.4		v
V _{ZCDT}	Triggering voltage (negative-going edge)	(3)		0.7		v
I _{ZCDb}	Input bias current	V _{ZCD} = 1 to 4.5 V		2		μA
I _{ZCDsrc}	Source current capability		-1.5			mA
I _{ZCDsnk}	Sink current capability		1.5			mA
Starter						
t _{START}	Start timer period		75	190	300	μs
Gate drive	r					
V _{OL}	Output low voltage	I _{sink} = 100 mA		0.6	1.2	V
V _{OH}	Output high voltage	I _{source} = 5 mA	9.5	10.3		V
I _{srcpk}	Peak source current		-0.6			А
I _{snkpk}	Peak sink current		0.8			Α
t _f	Voltage fall time			30	70	ns
t _r	Voltage rise time			60	130	ns
V _{Oclamp}	Output clamp voltage	I _{source} = 5 mA; Vcc = 20 V	10	12	15	V
	UVLO saturation	$Vcc = 0$ to V_{CCon} , $I_{sink} = 2$ mA			1.1	V

Electrical characteristics (continued) Table 5.

1. All the parameters are in tracking

2. The multiplier output is given by: $~V_{cs}=K\cdot V_{MULT}\cdot \left(V_{COMP}-2.5\right)$

3. Parameters guaranteed by design, functionality tested in production.